

M·C·C

Micro Commercial Components
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Features

- Oxide-Glass passivated Junction
- Bi-Directional protection in a single device
- Surge capabilities up to 80A@10/1000us or 250A@8/20us
- High Off-State impedance and Low On-State voltage
- Plastic material has UL flammability classification 94V -0

Mechanical Data

- Case : Molded plastic
- Polarity : None cathode band denotes
- Approx Weight : 0.093grams

Maximum Ratings

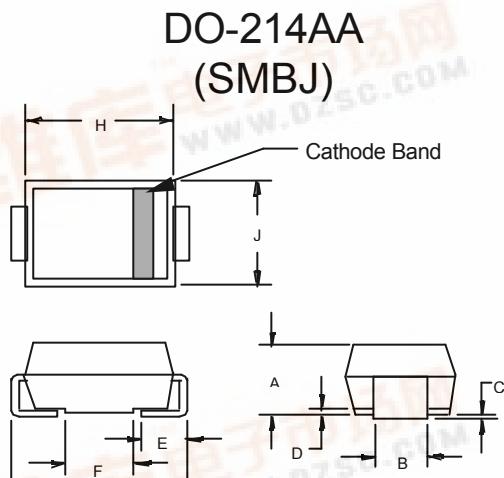
| Characteristic | Symbol | Value | Unit |
|--|----------------|-----------|-----------------------|
| Non-repetitive peak impulse current | I_{PP} | 80A | 10/1000us |
| Non-repetitive peak On-state current | I_{TSM} | 30A | 8.3ms, one-half cycle |
| Operating temperature range | T_{OP} | -40~150°C | |
| Junction and storage temperature range | T_J, T_{STG} | -55~150°C | |

Thermal Resistance

| Characteristic | Symbol | Value | Unit |
|--|----------------------------|--------------------|---------------------------|
| Thermal Resistance junction to lead | $R_{\theta JL}$ | 20°C/W | |
| Thermal Resistance junction to ambient | $R_{\theta JA}$ | 100°C/W | On recommended pad layout |
| Typical positive temperature coefficient for breakdown voltage | $\Delta V_{BR}/\Delta T_J$ | 0.1%/ $^{\circ}$ C | |

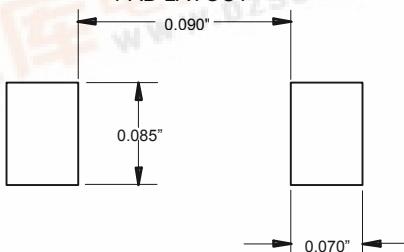
TSMBJ0505C-072

Transient Voltage Protection Device 65 Volts



| DIM | INCHES | | MM | | NOTE |
|-----|--------|------|------|------|------|
| | MIN | MAX | MIN | MAX | |
| A | .078 | .096 | 2.00 | 2.44 | |
| B | .077 | .083 | 1.96 | 2.10 | |
| C | .002 | .008 | .05 | .20 | |
| D | --- | .02 | --- | .51 | |
| E | .030 | .060 | .76 | 1.52 | |
| F | .065 | .091 | 1.65 | 2.32 | |
| G | .205 | .220 | 5.21 | 5.59 | |
| H | .160 | .180 | 4.06 | 4.57 | |
| J | .130 | .155 | 3.30 | 3.94 | |

SUGGESTED SOLDER PAD LAYOUT



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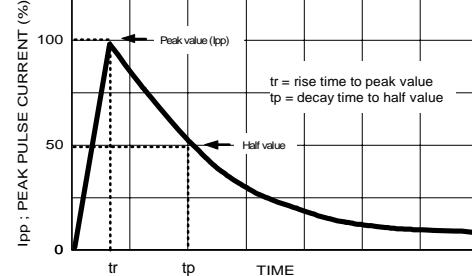
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ELECTRICAL CHARACTERISTIC @25°C Unless otherwise specified

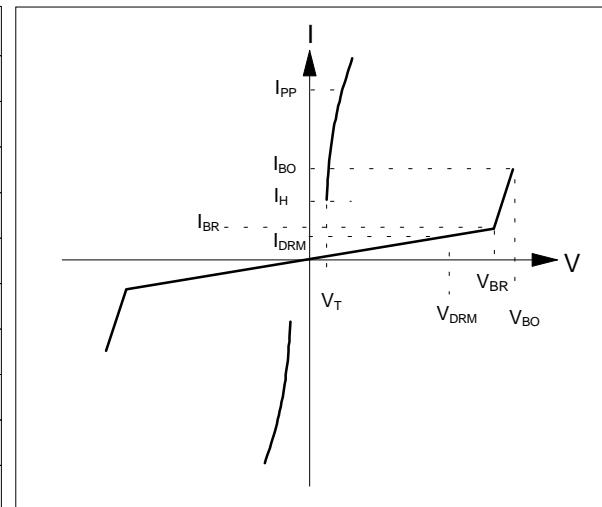
| Parameter | Rated Repetitive Off-state Voltage | Off-state Leakage Current@ V_{DRM} | Breakover Voltage | On-State Voltage @ $I_f=1.0A$ | Breakover Current | Holding Current | | Off-State Capacitance | |
|----------------|------------------------------------|--------------------------------------|-------------------|-------------------------------|-------------------|-----------------|-------|-----------------------|-------|
| Symbol | V_{DRM} | I_{DRM} | V_{BO} | V_T | I_{BO} | I_{BO+} | I_H | I_{H+} | C_J |
| Units | Volts | uA | Volts | Volts | mA | mA | mA | mA | pF |
| Limit | Max | Max | Max | Max | Min | Max | Min | Max | Typ. |
| TSMBJ0505C-072 | 65 | 5 | 88 | 5 | 50 | 800 | 150 | 800 | 140 |

MAXIMUM RATED SURGE WAVEFORM

| Waveform | Standard | I _{pp} (A) |
|------------|---------------|---------------------|
| 2/10 us | GR-1089-CORE | 250 |
| 8/20 us | IEC 61000-4-5 | 250 |
| 10/160 us | FCC Part 68 | 150 |
| 10/700 us | ITU-T K20/21 | 100 |
| 10/560 us | FCC Part 68 | 100 |
| 10/1000 us | GR-1089-CORE | 80 |



| Symbol | Parameter |
|-----------|--------------------------------------|
| V_{DRM} | Stand-off voltage |
| I_{DRM} | Leakage current at stand-off voltage |
| V_{BR} | Breakdown voltage |
| I_{BR} | Breakdown current |
| V_{BO} | Breakover voltage |
| I_{BO} | Breakover current |
| I_H | Holding current |
| V_T | On state voltage |
| I_{PP} | Peak pulse current |
| C_O | Off-state capacitance |



NOTE :

- $I_H > (V_L / R_L)$ If this criterion is not obeyed, the TSPD triggers but does not return correctly to high-resistance state. The surge recovery time. It does not exceed 30ms.
- Off-state capacitance measured at $f=1.0\text{MHz}$, 1.0Vrms signal, $VR=2\text{Vdc}$ bias.

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Fig.1 - Off-State Current v.s Junction Temperature

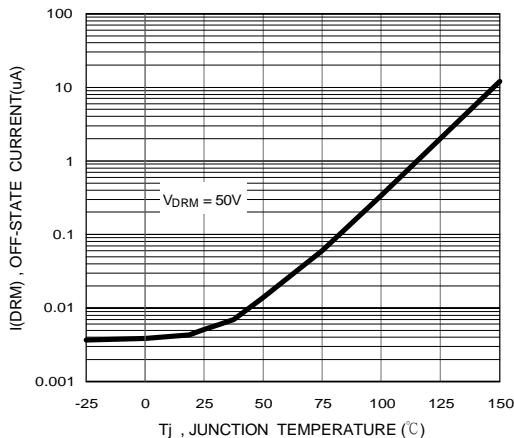


Fig.2 - Relative Variation of Breakdown Voltage v.s Junction Temperature

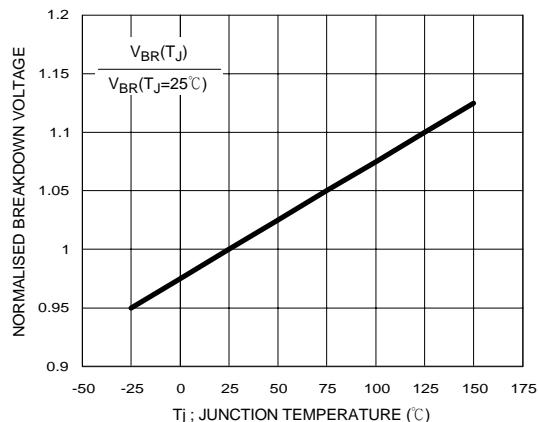


Fig.3 - Relative Variation of Breakover Voltage v.s Junction Temperature

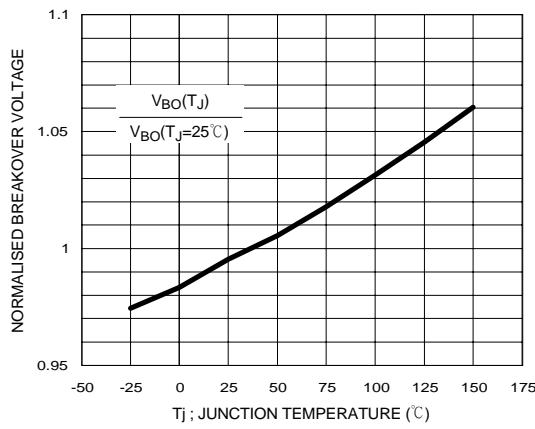


Fig.4 - On-State Current v.s On-State Voltage

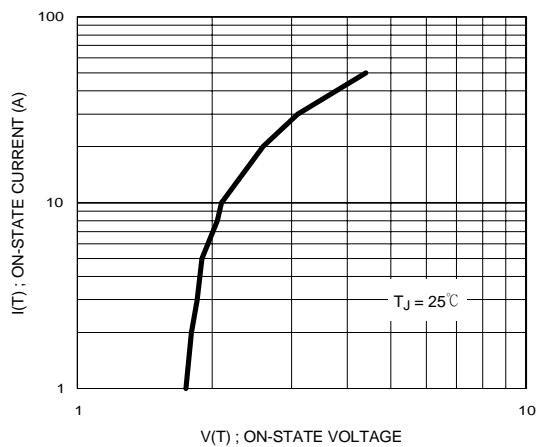


Fig.5 - Relative Variation of Holding Current v.s Junction Temperature

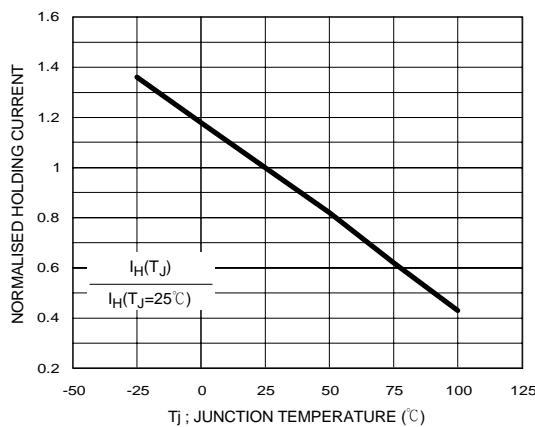
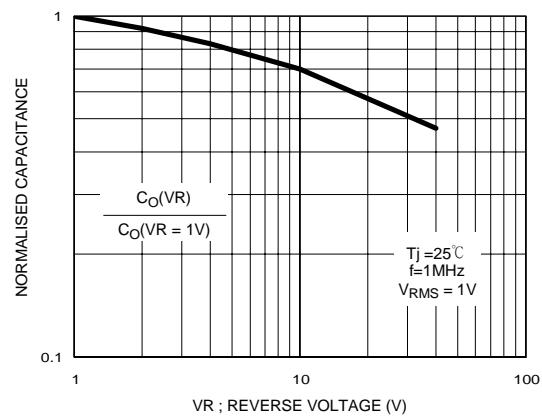


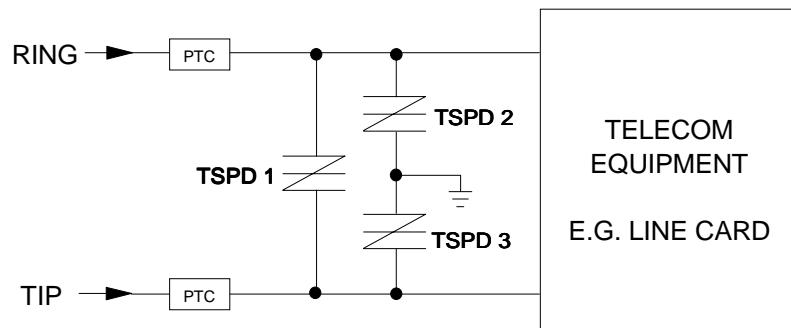
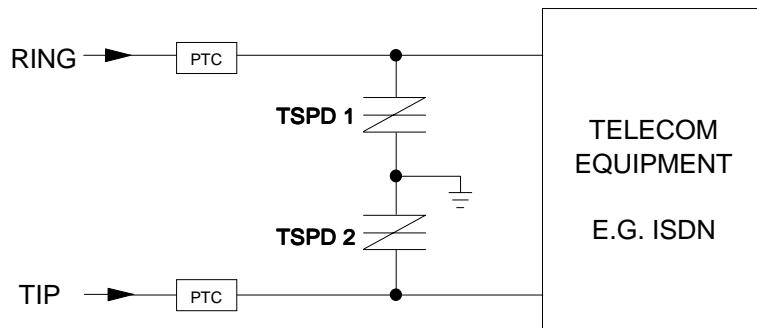
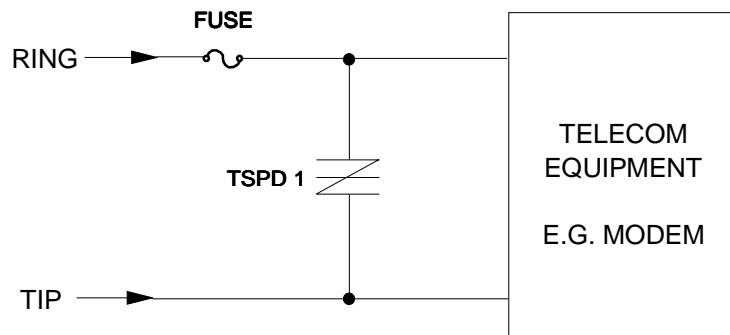
Fig.6 - Relative Variation of Junction Capacitance v.s Reverse Voltage Bias



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TYPICAL APPLICATION CIRCUITS



The PTC (Positive Temperature Coefficient) is an overcurrent protection device.